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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of

Atty. Ref.: 925-348

SUGAWARA

TC/A.U.: Unknown

11/04/2

Serial No. Unknown

Filed: August 7, 2006

Examiner: Unknown

For: HIGH-WITHSTAND VOLTAGE WIDE-GAP SEMICONDUCTOR DEVICE

AND POWER DEVICE

August 7, 2006

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

INFORMATION DISCLOSURE STATEMENT

As suggested by 37 C.F.R. 1.97, the undersigned attorney brings to the attention of the Patent and Trademark Office the references listed on the attached form PTO/SB/08a. A copy of each listed foreign patent document and article is attached.

This is not to be construed as a representation that a search has been made or that no better prior art exists, or that a reference is relevant merely because cited.

The Examiner is requested to initial the attached form PTO/SB/08a and to return a copy of the initialed document to the undersigned as an indication that the attached references have been considered and made of record.

Respectfully submitted,

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INFORMATION DISCLOSURE

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ATTY, DOCKET NO.

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APPLICANT

10588523 - GAU: 2818

SUGAWARA

(Use several sheets if necessary)

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August 7, 2006

-Unknown-

U.S. PATENT DOCUMENTS *EXAMINER **FILING DATE** CLASS SUBCLASS IF APPROPRIATE INITIAL DOCUMENT NUMBER DATE NAME 6,054,752 4/2000 Hara et al. /DHN/ (Corresponds to JP 11-074524) Shinohe et al. 5,969,400 10/1999 /DHN/ (Corresponds to JP 08-293618) FOREIGN PATENT DOCUMENTS TRANSLATION **DOCUMENT** DATE COUNTRY **CLASS SUBCLASS** YES /DHN/ 11-74524 3/1999 ŢР 7DHN/ 8-293618 11/1996 JР OTHER DOCUMENTS (including Author, Title, Date, Pertinent pages, etc.) /DHN/ International Search Report for PCT/JP2005/001705 dated 10 May 2005. Matsunami, Semiconductor SiC Technology and Applications, High-Withstand Voltage FET, Nikkan Kogyo Shimbunsha, /DHN/ March 31, 2003, pp. 218-221. Agarwal et al., Dynamic Performance of 3.1 kV 4H-SiC Asymmetical GTO Thyristors, Materials Science Forum, vols. /DHN/ 389-393, 2002, pp. 1349-1352. Chatty et al., Comparison of Nitrogen and Phosphorus Implanted, Planar, High-Voltage 4H-SiC Junction Rectifiers, /DHN/ Materials Science Forum, vols. 338-342, 2000, pp. 1331-1334. 11/04/2008 /Dao H Nguyen/ *Examiner Date Considered

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to application.